

#2A

In the Specification

Page 1, after the title, please insert the following paragraph.

This application is a **continuation** of patent application Serial No. 09/640,959 filed August 16, 2000.

*now abandoned*

Please replace the paragraph beginning at Page 1, Line 20 with the following replacement paragraph.

Two common conductive materials that may be included in a semiconductor manufacturing process are aluminum and copper. Such materials have been included in interconnect patterns and the like. However, it has been difficult to form small and/or high aspect ratio contacts with aluminum. Similarly, while copper can provide advantageously low resistance, it is believed that many technical problems may have to be overcome before copper contact structures may be practically implemented. In view of the above drawbacks to materials such as aluminum and copper, many conventional contact forming methods include tungsten as a contact filling material.

Please replace the paragraph beginning at Page 16, Line 17 with the following replacement paragraph.

Referring now to FIG. 1D, a tungsten film 005 may be deposited over a layered film of titanium/titanium nitride (003/004). A tungsten deposition step may include a mixed gas that includes a tungsten source gas, such as tungsten hexafluoride (WF<sub>6</sub>). In one particular arrangement, a tungsten film 005 may be deposited with chemical vapor deposition techniques at a temperature of about 400 °C and a pressure of about 6 Torr. Such a tungsten (W) chemical vapor deposition (CVD) step may form a layer of tungsten 005 over a layered film of titanium/titanium nitride (003/004), thereby filling a contact hole 020.